

MOVEABLE BARRIER FOR MULTIPLE ETCH PROCESSES

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ABSTRACT OF THE DISCLOSURE

A process chamber for a plasma processing apparatus is provided in which etch uniformity is maintained in both chemically driven and ion driven processes. The process chamber utilizes a barrier whose position relative to a wafer may be changed. During chemically driven processes, the barrier may be established so as to substantially prevent the diffusion of neutral reactants from regions outside the perimeter of the wafer. During ion driven processes, the barrier may be moved (e.g., withdrawn) so as to not compromise the ion driven etch.

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